

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MSC80915** is Designed for Class A, Common Emitter Applications to 2.3 GHz.

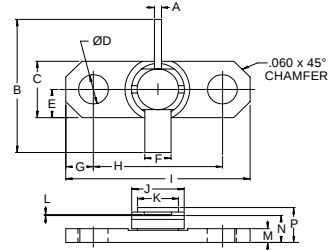
FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballasting

MAXIMUM RATINGS

I_C	300 mA
V_{CC}	20 V
P_{DISS}	5.0 W @ T _C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +200 °C
θ_{JC}	35 °C/W

PACKAGE STYLE .250 2L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.028 / 0.71	.032 / 0.81
B	.740 / 18.80	
C	.245 / 6.22	.255 / 6.48
D	.128 / 3.25	.132 / 3.35
E	.125 / 3.18	
F	.110 / 2.79	.117 / 2.97
G	.117 / 2.97	
H	.560 / 14.22	.570 / 14.48
I	.790 / 20.07	.810 / 20.57
J	.225 / 5.72	.235 / 5.97
K	.165 / 4.19	.185 / 4.70
L	.003 / 0.08	.007 / 0.18
M	.058 / 1.47	.068 / 1.73
N	.119 / 3.02	.135 / 3.43
P	.149 / 3.78	.187 / 4.75

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 1.0 mA	50			V
BV_{CEO}	I _C = 5.0 mA	20			V
BV_{EBO}	I _E = 1.0 mA	3.5			V
I_{CEO}	V _{CB} = 18 V			0.5	mA
h_{FE}	V _{CE} = 5.0 V I _C = 100 mA	15	85	120	---
C_{ob}	V _{CB} = 28 V f = 1.0 MHz			3.0	pF
P_g P_{1db}	V _{CE} = 18 V I _C = 140 mA fo = 2.0 GHz	7.5 +28	8.5		dB dBm